

# PROTECTION PRODUCTS

#### Description

The SMS series of TVS arrays are designed to protect sensitive electronics from damage or latch-up due to ESD and other voltage-induced transient events. Each device will protect up to four lines. They are available with operating voltages of 5V, 12V, 15V and 24V. They are unidirectional devices and may be used on lines where the signal polarities are above ground.

TVS diodes are solid-state devices designed specifically for transient suppression. They feature large crosssectional area junctions for conducting high transient currents. They offer desirable characteristics for board level protection including fast response time, low operating and clamping voltage and no device degradation.

The SMS series devices may be used to meet the immunity requirements of IEC 61000-4-2, level 4. The low cost SOT23-6L package makes them ideal for use in portable electronics such as cell phones, PDA's, and notebook computers.

#### Features

- ◆ Transient protection for data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns) IEC 61000-4-5 (Lightning) 24A (8/20µs)
- ◆ Small package for use in portable electronics
- Protects four I/O lines
- Working voltages: 5V, 12V, 15V and 24V
- Low leakage current
- Low operating and clamping voltages
- Solid-state silicon avalanche technology

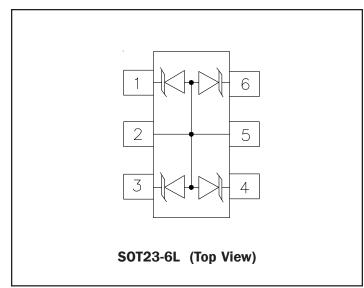
#### **Mechanical Characteristics**

- EIAJ SOT23-6L package
- Pb-Free, Halogen Free, RoHS/WEEE Compliant
- Lead Finish: Matte Sn
- Molding compound flammability rating: UL 94V-0
- Marking : Marking code
- ◆ Packaging : Tape and Reel

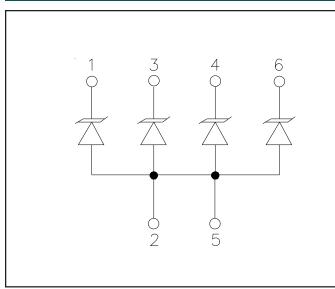
#### Applications

- Cell phone Handsets and Accessories
- Microprocessor Based Equipment
- Personal Digital Assistants (PDA's) and Pagers
- Desktops PC and Servers
- Notebook, Laptop, and Palmtop Computers
- Portable Instrumentation
- Peripherals
- MP3 Players

#### Schematic & PIN Configuration



#### Circuit Diagram





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### Absolute Maximum Rating

| Rating   | Symbol           | Value       | Units |
|--|------------------|-------------|-------|
| Peak Pulse Power (tp = 8/20µs)                                 | P <sub>pk</sub>  | 350         | Watts |
| ESD per IEC 61000-4-2 (Air)<br>ESD per IEC 61000-4-2 (Contact) | V <sub>ESD</sub> | 25<br>20    | kV    |
| Operating Temperature  | T,               | -55 to +125 | °C    |
| Storage Temperature  | T <sub>stg</sub> | -55 to +150 | °C    |

### **Electrical Characteristics**

| SMS05                     |                  |   |         |         |         |       |  |
|---------------------------|------------------|---|---------|---------|---------|-------|--|
| Parameter                 | Symbol           | Conditions  | Minimum | Typical | Maximum | Units |  |
| Reverse Stand-Off Voltage | V <sub>RWM</sub> |   |         |         | 5       | V     |  |
| Reverse Breakdown Voltage | V <sub>BR</sub>  | I <sub>t</sub> = 1mA  | 6       |         |         | V     |  |
| Reverse Leakage Current   | I <sub>R</sub>   | V <sub>RWM</sub> = 5V, T=25°C                                   |         |         | 20      | μA    |  |
| Clamping Voltage          | V <sub>c</sub>   | $I_{pp} = 5A, t_p = 8/20 \mu s$                                 |         |         | 9.8     | V     |  |
| Clamping Voltage          | V <sub>c</sub>   | $I_{pp} = 24A, t_p = 8/20\mu s$                                 |         |         | 14.5    | V     |  |
| Peak Pulse Current        | I <sub>PP</sub>  | t <sub>p</sub> = 8/20µs   |         |         | 24      | А     |  |
| Junction Capacitance      | C <sub>j</sub>   | Between I/O Pins and<br>Ground<br>V <sub>R</sub> = OV, f = 1MHz |         | 325     | 400     | pF    |  |

| SMS12                     |                  |   |         |         |         |       |  |
|---------------------------|------------------|---|---------|---------|---------|-------|--|
| Parameter                 | Symbol           | Conditions  | Minimum | Typical | Maximum | Units |  |
| Reverse Stand-Off Voltage | V <sub>RWM</sub> |   |         |         | 12      | V     |  |
| Reverse Breakdown Voltage | V <sub>BR</sub>  | I <sub>t</sub> = 1mA  | 13.3    |         |         | V     |  |
| Reverse Leakage Current   | I <sub>R</sub>   | V <sub>RWM</sub> = 12V, T=25°C                                  |         |         | 1       | μA    |  |
| Clamping Voltage          | V <sub>c</sub>   | $I_{pp} = 5A, t_p = 8/20 \mu s$                                 |         |         | 19      | V     |  |
| Clamping Voltage          | V <sub>c</sub>   | I <sub>pp</sub> = 15Α, t <sub>p</sub> = 8/20μs                  |         |         | 23      | V     |  |
| Peak Pulse Current        | I <sub>PP</sub>  | t <sub>p</sub> = 8/20µs   |         |         | 15      | А     |  |
| Junction Capacitance      | C <sub>j</sub>   | Between I/O Pins and<br>Ground<br>V <sub>R</sub> = OV, f = 1MHz |         | 135     | 150     | pF    |  |

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# SMS05 through SMS24

### **PROTECTION PRODUCTS**

### Electrical Characteristics (Continued)

#### SMS15

| 301313                    |                  |   |         |         |         |       |
|---------------------------|------------------|---|---------|---------|---------|-------|
| Parameter                 | Symbol           | Conditions  | Minimum | Typical | Maximum | Units |
| Reverse Stand-Off Voltage | V <sub>RWM</sub> |   |         |         | 15      | V     |
| Reverse Breakdown Voltage | V <sub>BR</sub>  | I <sub>t</sub> = 1mA  | 16.7    |         |         | V     |
| Reverse Leakage Current   | I <sub>R</sub>   | V <sub>RWM</sub> = 15V, T=25°C                                  |         |         | 1       | μA    |
| Clamping Voltage          | V <sub>c</sub>   | $I_{pp} = 5A, t_p = 8/20 \mu s$                                 |         |         | 24      | V     |
| Clamping Voltage          | V <sub>c</sub>   | I <sub>pp</sub> = 12A, t <sub>p</sub> = 8/20µs                  |         |         | 29      | V     |
| Peak Pulse Current        | I <sub>PP</sub>  | t <sub>p</sub> = 8/20µs   |         |         | 12      | А     |
| Junction Capacitance      | C <sub>j</sub>   | Between I/O Pins and<br>Ground<br>V <sub>R</sub> = OV, f = 1MHz |         | 100     | 125     | pF    |

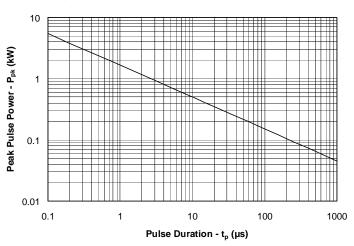
| SMS24                     |                  |   |         |         |         |       |  |
|---------------------------|------------------|---|---------|---------|---------|-------|--|
| Parameter                 | Symbol           | Conditions  | Minimum | Typical | Maximum | Units |  |
| Reverse Stand-Off Voltage | V <sub>RWM</sub> |   |         |         | 24      | V     |  |
| Reverse Breakdown Voltage | V <sub>BR</sub>  | I <sub>t</sub> = 1mA  | 26.7    |         |         | V     |  |
| Reverse Leakage Current   | I <sub>R</sub>   | V <sub>RWM</sub> = 24V, T=25°C                                  |         |         | 1       | μA    |  |
| Clamping Voltage          | V <sub>c</sub>   | $I_{pp} = 5A, t_p = 8/20 \mu s$                                 |         |         | 40      | V     |  |
| Clamping Voltage          | V <sub>c</sub>   | $I_{pp} = 8A, t_p = 8/20 \mu s$                                 |         |         | 44      | V     |  |
| Peak Pulse Current        | I <sub>PP</sub>  | t <sub>p</sub> = 8/20µs   |         |         | 8       | А     |  |
| Junction Capacitance      | C <sub>j</sub>   | Between I/O Pins and<br>Ground<br>V <sub>R</sub> = OV, f = 1MHz |         | 60      | 75      | pF    |  |



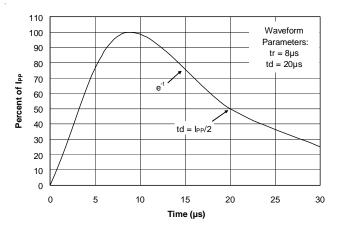
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#### **Typical Characteristics**

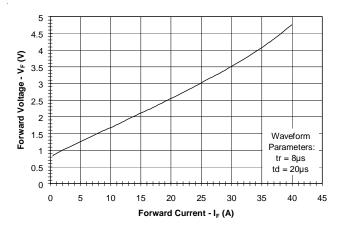
#### Non-Repetitive Peak Pulse Power vs. Pulse Time

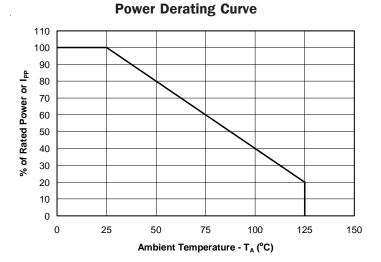




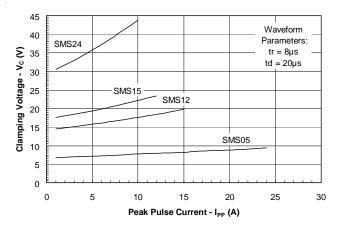


Forward Voltage vs. Forward Current





#### **Clamping Voltage vs. Peak Pulse Current**





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#### Applications Information

#### **Device Connection for Protection of Four Data Lines**

The SMSxx is designed to protect up to four unidirectional data lines. The device is connected as follows:

 Unidirectional protection of four I/O lines is achieved by connecting pins 1, 3, 4 and 6 to the data lines. Pin 2 and 5 are connected to ground. The ground connections should be made directly to the ground plane for best results. The path length is kept as short as possible to reduce the effects of parasitic inductance in the board traces.

# Circuit Board Layout Recommendations for Suppression of ESD

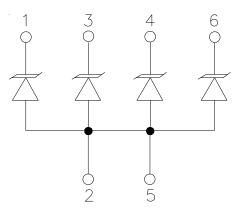
Good circuit board layout is critical for the suppression of ESD induced transients. The following guidelines are recommended:

- Place the SMSxx near the input terminals or connectors to restrict transient coupling.
- Minimize the path length between the SMSxx and the protected line.
- Minimize all conductive loops including power and ground loops.
- The ESD transient return path to ground should be kept as short as possible.
- Never run critical signals near board edges.
- Use ground planes whenever possible.

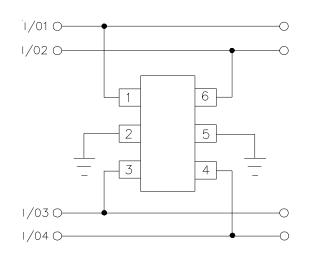
#### **Matte Tin Lead Finish**

Matte tin has become the industry standard lead-free replacement for SnPb lead finishes. A matte tin finish is composed of 100% tin solder with large grains. Since the solder volume on the leads is small compared to the solder paste volume that is placed on the land pattern of the PCB, the reflow profile will be determined by the requirements of the solder paste. Therefore, these devices are compatible with both lead-free and SnPb assembly techniques. In addition, unlike other lead-free compositions, matte tin does not have any added alloys that can cause degradation of the solder joint.





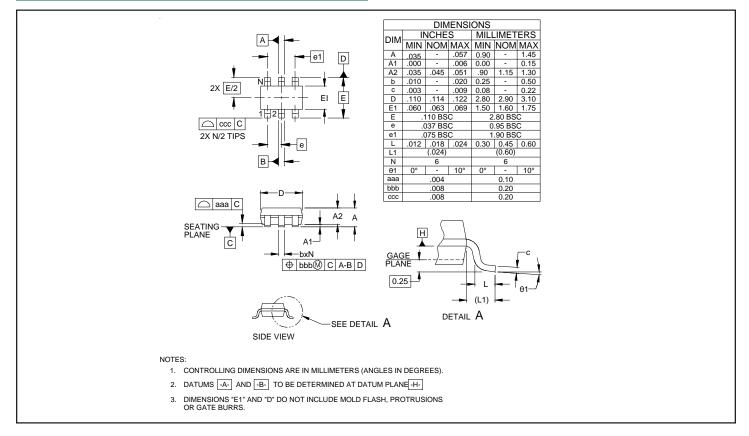
#### **Protection of Four Unidirectional Lines**





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#### Outline Drawing -SOT23 6L



#### Land Pattern -SOT23 6L

